

ABSTRACT OF THE DISCLOSURE

Thin-layer electronic device, in particular a thin-layer power device, and process for fabricating
5 this device.

According to the invention, an electronic device is formed comprising an active part (38,40,42), a first thin layer (36) which is made of a semiconductor material and in which this active part is formed, and a
10 substrate (44) which is made of a conductive material. This device also comprises a carrier recombination zone(46) which is located between the substrate and the first thin layer and which also ensures a resistive electric contact between this substrate and this first
15 thin layer.

Figures 5A to 5D.